



#### **Features and Benefits**

- Exceptional reliability
- Small fully-molded SIP package with heatsink mounting for high thermal dissipation and long life
- V<sub>DRM</sub> of 400 or 600 V
- 25 A<sub>RMS</sub> on-state current
- Uniform switching
- UL Recognized Component (File No.: E118037) (suffix I)



### Package: 3-pin SIP (TO-3PF)



### **Description**

This Sanken triac (bidirectional triode thyristor) is designed for AC power control, providing reliable, uniform switching for full-cycle AC applications.

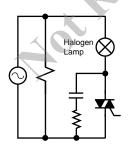
In comparison with other products on the market, the TMA25x series provides increased isolation voltage (2000 VAC<sub>RMS</sub>), guaranteed for up to 1 minute, and greater peak nonrepetitive off-state voltage,  $V_{DSM}$  (700 V). In addition, commutation dv/dt and (dv/dt)c are improved.

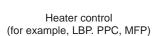
### **Applications**

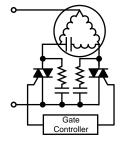
- Residential and commercial appliances: vacuum cleaners, rice cookers, TVs, home entertainment
- White goods: washing machines
- Office automation power control, photocopiers
- Motor control for small tools
- Temperature control, light dimmers, electric blankets
- General use switching mode power supplies (SMPS)

Not to scale

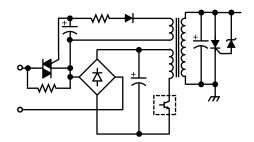
## **Typical Applications**







Two-phase motor control (for example, washing machine)



In-rush current control (for example, SMPS)

# Triac (Bidirectional Triode Thyristor)

#### **Selection Guide**

Part Number	V <sub>DRM</sub> (V)	UL-Recognized Component	Package	Packing
TMA254B(I)	400	Yes		
TMA254B-L	400	-	3-pin fully molded SIP with	20 piagos par tuba
TMA256B(I)	600	Yes	heatsink mount	30 pieces per tube
TMA256B-L	600	-		

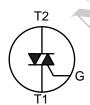
#### **Absolute Maximum Ratings**

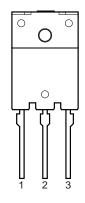
Characteristic	Symbol		Notes	Rating	Units
Dool Donatition Off Chata Valtage	$V_{DRM}$	TMA254Bx	• 0	400	V
Peak Repetitive Off-State Voltage		TMA256Bx	R <sub>GREF</sub> = ∞	600	V
Dool Nee Donation Off Chata Valtage	$V_{DSM}$	TMA254Bx	R <sub>GREF</sub> = ∞	500	V
Peak Non-Repetitive Off-State Voltage		TMA256Bx		700	V
Isolation Voltage	V <sub>ISO</sub>	AC RMS appl	lied for 1 minute between lead and case	2000	V
RMS On-State Current	I <sub>T(RMS)</sub>		50/60 Hz full cycle sine wave, total Conduction angle ( $\alpha$ +) + ( $\alpha$ -) = 360°, $T_C$ = 83°C		А
Surge On-State Current	I <sub>TSM</sub>	f = 60 Hz	Full cycle sine wave, peak value, non-repetitive, initial $T_J = 125^{\circ}C$	263	А
		f = 50 Hz		250	А
I²t Value for Fusing	l²t	Value for 50 Hz half cycle sine wave, 1 cycle, I <sub>TSM</sub> = 250 A		312	A <sup>2</sup> •s
Critical Rising Rate of On-State Current	di/dt	$I_T = I_{T(RMS)} \times \sqrt{2}, V_D = V_{DRM} \times 0.5, f \le 60 \text{ Hz}, t_{gw} \ge 100  \mu\text{s}, t_{gr} \le 250 \text{ ns}, I_{gp} \ge 60 \text{ mA}$		25	A/µs
Peak Gate Current	I <sub>GM</sub>	f ≥ 50 Hz, duty cycle ≤ 10%		2	Α
Peak Gate Power Dissipation	P <sub>GM</sub>	f ≥ 50 Hz, duty cycle ≤ 10%		5	W
Average Gate Power Dissipation	P <sub>GM(AV)</sub>	$T_J < T_J(max)$		0.5	W
Junction Temperature	TJ			-40 to 125	°C
Storage Temperature	T <sub>stg</sub>			-40 to 125	°C

### Thermal Characteristics May require derating at maximum conditions

Characteristic	Symbol	Test Conditions	Value	Units
Package Thermal Resistance (Junction to Case)	$R_{ heta JC}$	For AC	1.5	°C/W

# Pin-out Diagram





#### **Terminal List Table**

Number	Name	Function	
1	T1	Main terminal, gate referenced	
2	T2	Main terminal connect to signal side	
3	G	Gate control	

All performance characteristics given are typical values for circuit or system baseline design only and are at the nominal operating voltage and an ambient temperature,  $T_A$ , of 25°C, unless otherwise stated.





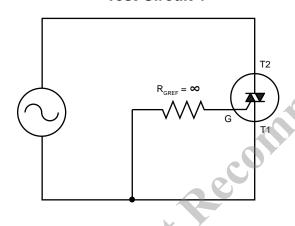
# Triac (Bidirectional Triode Thyristor)

#### **ELECTRICAL CHARACTERISTICS**

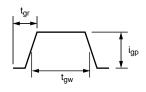
Characteristics	Symbol	Test Conditions		Min.	Тур.	Max.	Unit
Off-State Leakage Current I <sub>DRM</sub>		$V_D = V_{DRM}, T_J = 125$ °C	<sub>D</sub> = V <sub>DRM</sub> , T <sub>J</sub> = 125°C, R <sub>GREF</sub> = ∞ using test circuit 1		_	2.0	mA
		V <sub>D</sub> = V <sub>DRM</sub> , T <sub>J</sub> = 25°C, R <sub>GREF</sub> = ∞ using test circuit 1		-	-	100	μΑ
On-State Voltage	V <sub>TM</sub>	I <sub>T</sub> = 20 A, T <sub>J</sub> = 25°C		-	-	1.4	V
		Quadrant I: T2+, G+	$V_D = 12 \text{ V}, R_L = 20 \Omega, T_J = 25^{\circ}\text{C}$	-	-	1.5	V
Gate Trigger Voltage	V <sub>GT</sub>	Quadrant II: T2+, G-		-	-	1.5	V
		Quadrant III: T2-, G-		-	-<	1.5	V
Gate Trigger Current	I <sub>GT</sub>	Quadrant I: T2+, G+	$V_D = 12 \text{ V}, R_L = 20 \Omega, T_J = 25^{\circ}\text{C}$	_		30	mA
		Quadrant II: T2+, G-		- 0	20	30	mA
		Quadrant III: T2-, G-		-0	₹ -	30	mA
Gate Non-trigger Voltage	$V_{GD}$	$V_D = V_{DRM} \times 0.5, R_L = 4 k\Omega, T_J = 125 ^{\circ}C$		0.2	-	-	V
Critical Rising Rate of Off-State Voltage during Commutation*	(dv/dt)c	$T_J = 125$ °C, $V_D = 400$ V, $(di/dt)c = -12$ A/ms, $I_{TP} = 2$ A		_	V/µs		
Critical Rising Rate of Off-StateVoltage	dv/dt	$V_D = V_{DRM} \times 0.66$ , $T_J = 125$ °C, $R_{GREF} = \infty$ using test circuit 1 100 – –		V/µs			

<sup>\*</sup>Where  $I_{TP}$  is the peak current through T2 to T1.

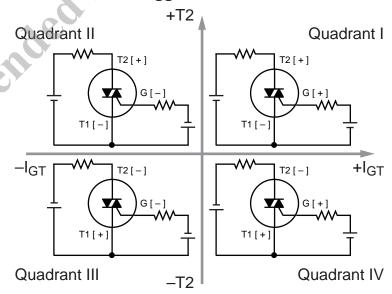
### **Test Circuit 1**



## **Gate Trigger Current**



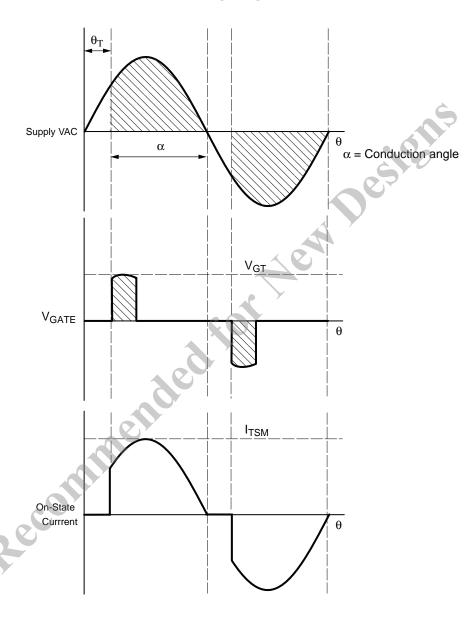
### **Gate Trigger Characteristics**



Polarities referenced to T1



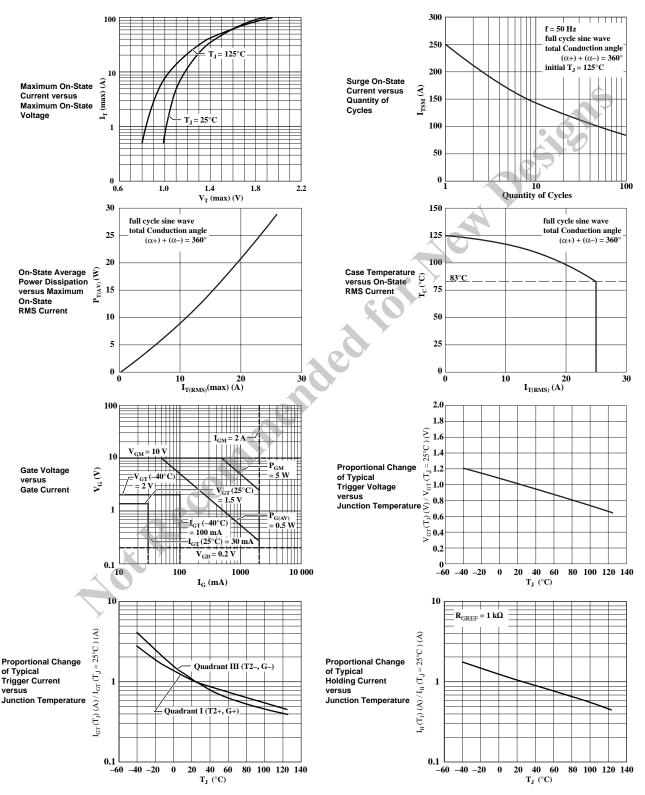
### **Commutation Timing Diagrams**





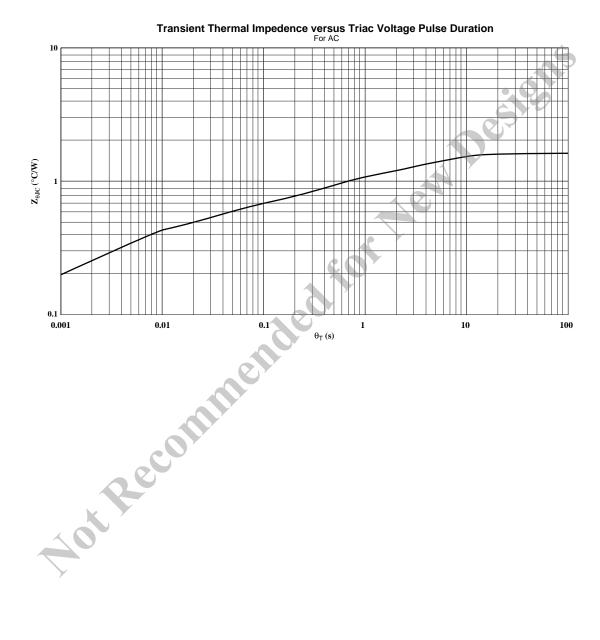


### Performance Characteristics at $T_A = 25$ °C





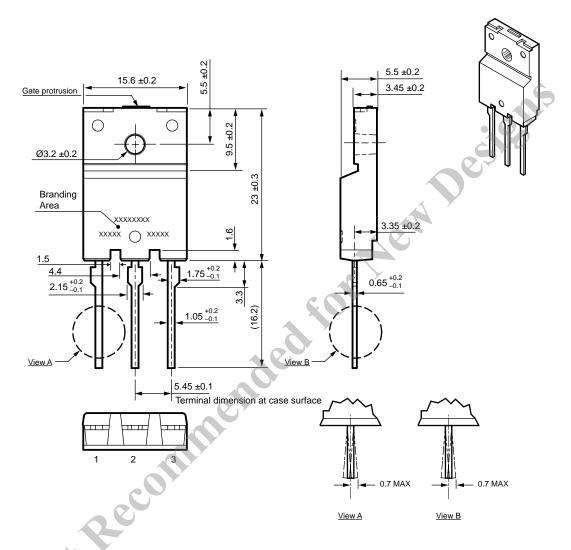








### **TO-3PF Package Outline Drawing**



Gate burr: 0.3 mm (max.), mold flash may appear at opposite side

Terminal core material: Cu

Terminal treatment: Ni plating and Pb-free solder dip

Leadform: 700

Package: TO-3PF (FM100)

Dimensions in millimeters

Branding codes (exact appearance at manufacturer discretion):

1st line, type: MA25xB 2nd line left, lot: YM

Where: Y is the last digit of the year of manufacture

M is the month (1 to 9, O, N, D)

2nd line right, lot: DD

Where: DD is the date



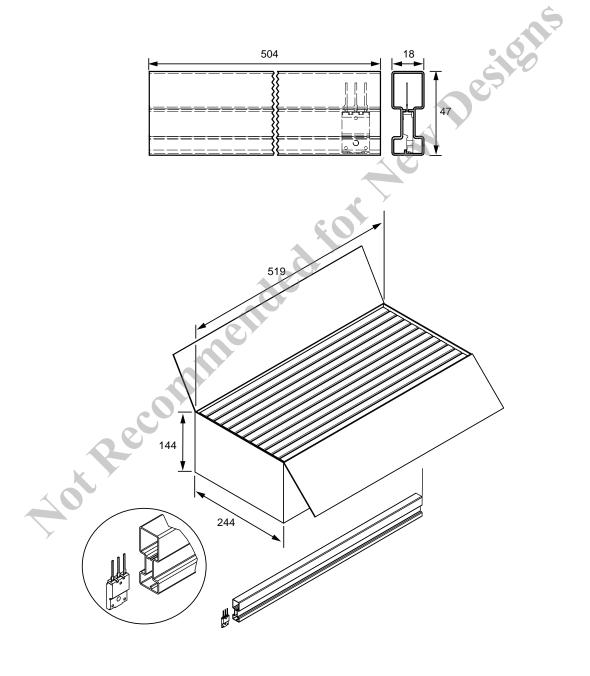
Leadframe plating Pb-free. Device meets RoHS requirements.





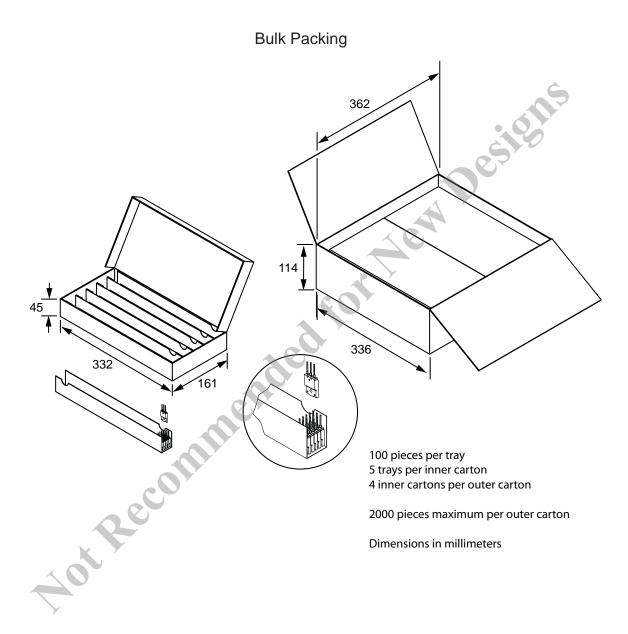
## **Packing Specification**

**Tube Packing** 













# Triac (Bidirectional Triode Thyristor)



**WARNING** — These devices are designed to be operated at lethal voltages and energy levels. Circuit designs that embody these components must conform with applicable safety requirements. Precautions must be taken to prevent accidental contact with power-line potentials. Do not connect grounded test equipment.

The use of an isolation transformer is recommended during circuit development and breadboarding.

Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

#### **Cautions for Storage**

- Ensure that storage conditions comply with the standard temperature (5°C to 35°C) and the standard relative humidity (around 40 to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of products that have been stored for a long time.

#### **Cautions for Testing and Handling**

When tests are carried out during inspection testing and other standard test periods, protect the products from power surges from the testing device, shorts between adjacent products, and shorts to the heatsink.

#### Remarks About Using Silicone Grease with a Heatsink

- When silicone grease is used in mounting this product on a heatsink, it shall be applied evenly and thinly. If more silicone grease than required is applied, it may produce stress.
- Coat the back surface of the product and both surfaces of the insulating plate to improve heat transfer between the product and the heatsink.
- Volatile-type silicone greases may permeate the product and produce cracks after long periods of time, resulting in reduced heat radiation effect, and possibly shortening the lifetime of the product.
- Our recommended silicone greases for heat radiation purposes, which will not cause any adverse effect on the product life, are indicated below:

Type	Suppliers
G746	Shin-Etsu Chemical Co., Ltd.
YG6260	Momentive Performance Materials
SC102	Dow Corning Toray Silicone Co., Ltd.

#### **Heatsink Mounting Method**

- Torque When Tightening Mounting Screws. Thermal resistance increases when tightening torque is low, and radiation effects are decreased. When the torque is too high, the screw can strip, the heatsink can be deformed, and distortion can arise in the product frame. To avoid these problems, observe the recommended tightening torques for this product package type 0.686 to 0.882 Nem (7 to 9 kgfecm).
- Diameter of Heatsink Hole: < 4 mm. The deflection of the press mold when making the hole may cause the case material to crack at the joint with the heatsink. Please pay special attention for this effect.

#### Soldering

 When soldering the products, please be sure to minimize the working time, within the following limits:

260±5°C 10 s 350±5°C 3 s

 Soldering iron should be at a distance of at least 1.5 mm from the body of the products

#### **Electrostatic Discharge**

- When handling the products, operator must be grounded. Grounded wrist straps worn should have at least 1 MΩ of resistance to ground to prevent shock hazard.
- Workbenches where the products are handled should be grounded and be provided with conductive table and floor mats.
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the products, the head of soldering irons or the solder bath must be grounded in other to prevent leak voltages generated by them from being applied to the products.
- The products should always be stored and transported in our shipping containers or conductive containers, or be wrapped in aluminum foil.





# Triac (Bidirectional Triode Thyristor)



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Sanken and Allegro reserve the right to make, from time to time, such departures from the detail specifications as may be required to permit improvements in the performance, reliability, or manufacturability of its products. Therefore, the user is cautioned to verify that the information in this publication is current before placing any order.

When using the products described herein, the applicability and suitability of such products for the intended purpose shall be reviewed at the users responsibility.

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# Triac (Bidirectional Triode Thyristor)

#### **Worldwide Contacts**

#### Asia-Pacific

#### China

### Sanken Electric Hong Kong Co., Ltd.

Suite 1026, Ocean Centre Canton Road, Tsimshatsui Kowloon, Hong Kong

Tel: 852-2735-5262, Fax: 852-2735-5494

### Sanken Electric (Shanghai) Co., Ltd.

Room 3202, Maxdo Centre Xingyi Road 8, Changning District Shanghai, China

Tel: 86-21-5208-1177, Fax: 86-21-5208-1757

### Taiwan Sanken Electric Co., Ltd.

Room 1801, 18th Floor 88 Jung Shiau East Road, Sec. 2 Taipei 100, Taiwan R.O.C.

Tel: 886-2-2356-8161, Fax: 886-2-2356-8261

#### Japan

### Sanken Electric Co., Ltd. Overseas Sales Headquarters

Metropolitan Plaza Building 1-11-1 Nishi-Ikebukuro, Toshima-ku Tokyo 171-0021, Japan

Tel: 81-3-3986-6164, Fax: 81-3-3986-8637

#### Korea

#### Sanken Electric Korea Co., Ltd.

Samsung Life Yeouido Building 16F 23-10, Yeouido-Dong, Yeongdeungpo-gu Seoul 150-734, Korea Tel: 82-2-714-3700, Fax: 82-2-3272-2145

### Singapore

### Sanken Electric Singapore Pte. Ltd.

150 Beach Road, #14-03 The Gateway West Singapore 189720

Tel: 65-6291-4755, Fax: 65-6297-1744

### <u>Europe</u>

#### Sanken Power Systems (UK) Limited

Pencoed Technology Park Pencoed, Bridgend CF35 5HY, United Kingdom Tel: 44-1656-869-100, Fax: 44-1656-869-162

### North America

#### **United States**

### Allegro MicroSystems, Inc.

115 Northeast Cutoff Worcester, Massachusetts 01606, U.S.A. Tel: 1-508-853-5000, Fax: 1-508-853-7895

#### Allegro MicroSystems, Inc.

14 Hughes Street, Suite B105 Irvine, California 92618, U.S.A.

Tel: 1-949-460-2003, Fax: 1-949-460-7837



